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Figures

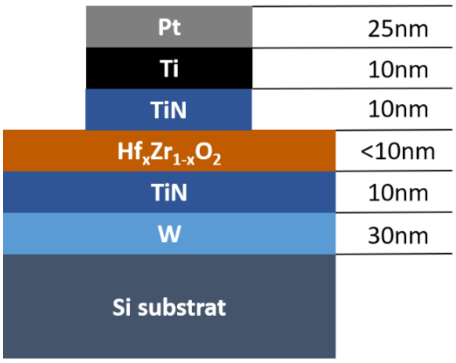

Figure 1: Investigated capacitor stack with ALD deposited $Hf_xZr_{1-x}O_2$

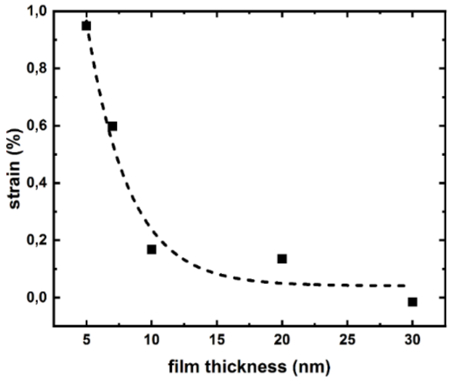

Figure 2: Analysis of strain evolution during thickness scaling of ALD $Hf_{0.5}Zr_{0.5}O_2$ films

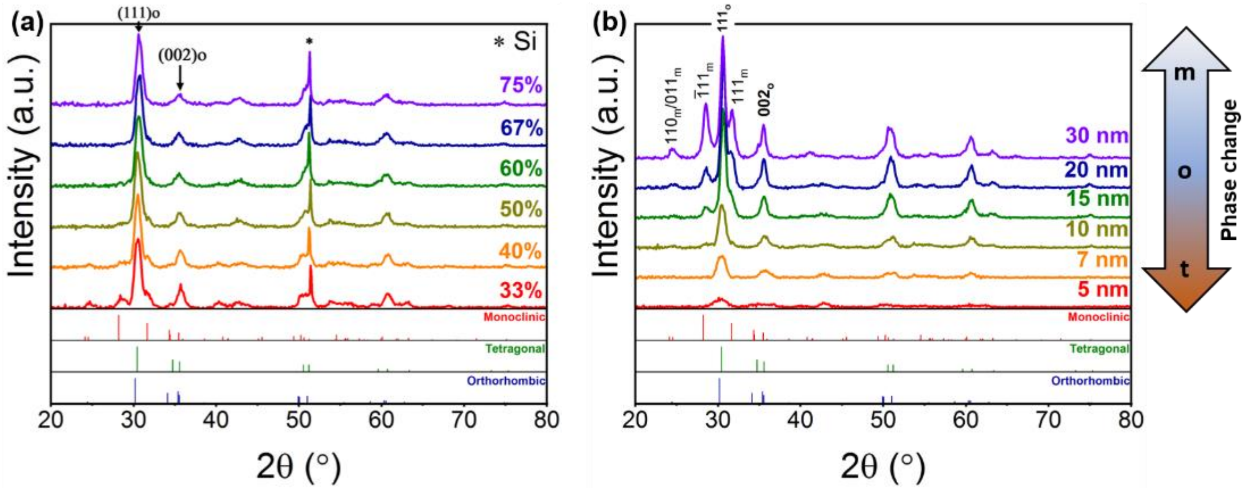

Figure 3: GIXRD results of (a) Zr doping series and (b) $Hf_{0.5}Zr_{0.5}O_2$ thickness split to distinguish phase transition

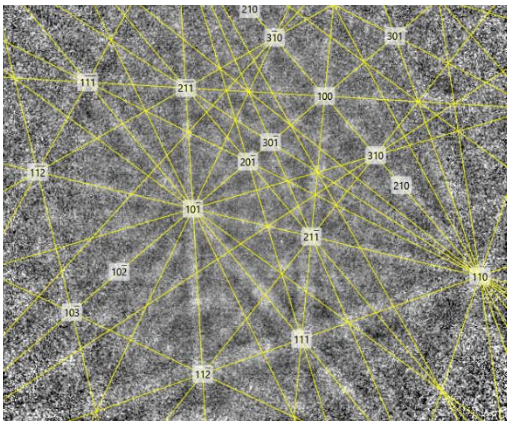

Figure 4: EBSD analysis on 10nm ferroelectric o-phase of $Hf_{0.5}Zr_{0.5}O_2$